
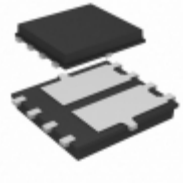
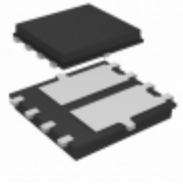
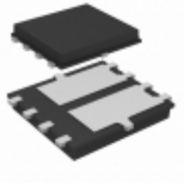
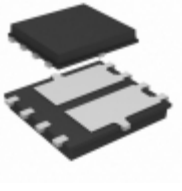
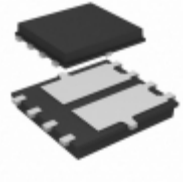
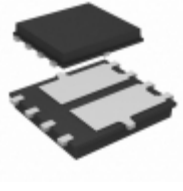
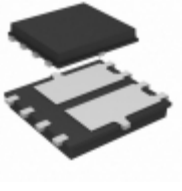
	<h2>SI7909DN-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7909DN-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET 2P-CH 12V 5.3A 1212-8</p> <p>Datenblätter:  SI7909DN-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 6000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7909DN-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET 2P-CH 12V 5.3A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	6000 pcs Stock
detaillierte Beschreibung	Mosfet Array 2 P-Channel (Dual) 12V 5.3A 1.3W
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.3W
Verpackung / Gehäuse	PowerPAK® 1212-8 Dual
Supplier Device-Gehäuse	PowerPAK® 1212-8 Dual
Typ FET	2 P-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	5.3A
Rds On (Max) @ Id, Vgs	37 mOhm @ 7.7A, 4.5V
VGS (th) (Max) @ Id	1V @ 700µA
Gate Charge (Qg) (Max) @ Vgs	24nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

SI7909DN-T1-GE3 ist neu im Original, Suche SI7909DN-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7909DN-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7909DN-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7911DN-T1-E3 Vishay / Siliconix MOSFET 2P-CH 20V 4.2A 1212-8</p>	 <p>SI7911DN-T1-GE3 Vishay / Siliconix MOSFET 2P-CH 20V 4.2A 1212-8</p>	 <p>SI7905DN-T1-GE3 Vishay / Siliconix MOSFET 2P-CH 40V 6A PPAK 1212-8</p>	 <p>SI7905DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2P-CH 40V 6A PPAK 1212-8</p>
 <p>SI7909DN-T1-GE3 Vishay / Siliconix MOSFET 2P-CH 12V 5.3A 1212-8</p>	 <p>SI7909DN-T1-E3 Vishay / Siliconix MOSFET 2P-CH 12V 5.3A 1212-8</p>	 <p>SI7911DN-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2P-CH 20V 4.2A 1212-8</p>	 <p>SI7911DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2P-CH 20V 4.2A 1212-8</p>

heiße Teile

Mehr

 SI7900AEDN-T1-E3	 SI7900AEDN-T1-GE3	 SI7900AEDN-T1-GE3	 SI7900AEDN-T1-GE3	 SI7900EDN
 SI7900EDN-T1	 SI7900EDN-T1-E3	 SI7900EDN-T1-GE3	 SI7901EDN-T1	 SI7901EDN-T1-E3
 SI7901EDN-T1-E3	 SI7904BDN-T1-E3	 SI7904BDN-T1-E3	 SI7904BDN-T1-GE3	 SI7904BDN-T1-GE3
 SI7904DN	 SI7904DN-T1	 SI7904DN-T1-E3	 SI7904DN-T1-E3	 SI7904DN-T1-GE3
 SI7904DN-T1-GE3	 SI7905DN-T1-GE3	 SI7905DN-T1-GE3	 SI7909DN-T1-E3	 SI7909DN-T1-E3
 SI7909DN-T1-GE3	 SI7911DN	 SI7911DN-T1-E3	 SI7911DN-T1-E3	 SI7911DN-T1-E3
 SI7911DN-T1-GE3	 SI7913DN-T1-E3	 SI7913DN-T1-E3	 SI7913DN-T1-GE3	 SI7913DN-T1-GE3
 SI7922DN-T1-E3	 SI7922DN-T1-E3	 SI7922DN-T1-GE3	 SI7922DN-T1-GE3	 SI7923DN-T1-E3
 SI7923DN-T1-E3	 SI7923DN-T1-GE3	 SI7923DN-T1-GE3	 SI7938DP-T1-GE3	 SI7938DP-T1-GE3
 SI7940DP	 SI7940DP-T1-E3	 SI7940DP-T1-E3	 SI7941DP-T1-E3	 SI7941DP-T1-GE3

Contact us: Info@Y-IC.com

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